

N-channel 25 V 0.99 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 2 — 4 July 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads
- Ultra low Rdson and low parasitic inductance

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	25	V
I _D	drain current	T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	272	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R _{DSon} drain-source on-state resistance		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{}$		-	0.95	1.25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_i = 25 ^{\circ}\text{C}; \text{ see Figure 12}$		-	0.75	0.99	mΩ



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic c	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15};$ see Figure 15	-	14	-	nC
Q _{G(tot)}	total gate charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 12 \text{ V}; \text{ see } \frac{\text{Figure } 15}{\text{Figure } 14};$	-	51	-	nC

^[1] Continuous current is limited by package

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	S	source		5		
2	S	source	mb	D		
3	S	source				
4	G	gate	9			
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S		

SOT669 (LFPAK; Power-SO8)

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN0R9-25YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

	_					
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	25	V
V_{DGR}	drain-gate voltage	$25 \text{ °C} \le T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	25	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	100	Α
		T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; see <u>Figure 4</u>		-	1563	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	272	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)		920	-	V
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C	[1]	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1563	Α
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 25 V; unclamped; R_{GS} = 50 Ω ; see Figure 3		-	342	mJ

[1] Continuous current is limited by package

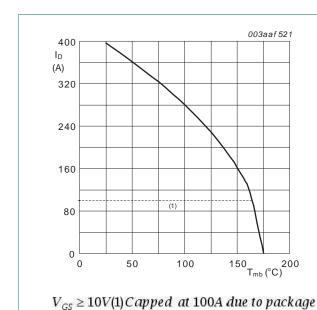


Fig 1. Continuous drain current as a function of mounting base temperature

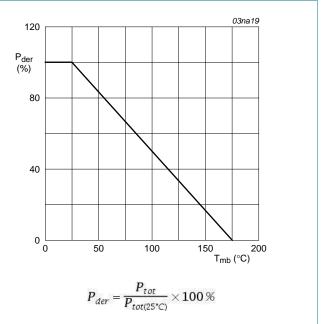


Fig 2. Normalized total power dissipation as a function of mounting base temperature

PSMN0R9-25YLC

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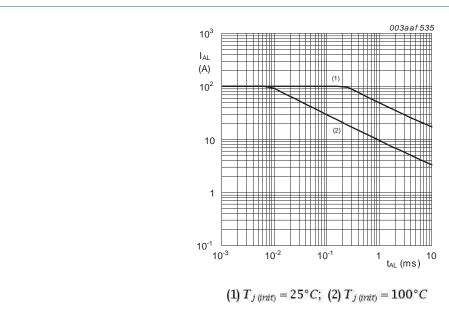
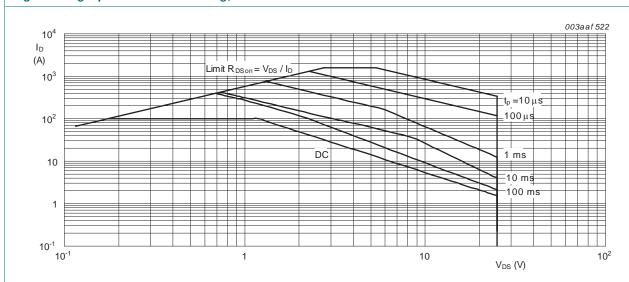


Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



 $T_{mb} = 25$ °C; I_{DM} is a single pulse

Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	0.45	0.55	K/W



6. Characteristics

Table 6. Characteristics

Symbol Static charact V _{(BR)DSS}		Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}						
V _{(BR)DSS}		1 050 A W 0 T 0500	05			.,
	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{V}; T_j = 25 ^{\circ}\text{C}$	25	-	-	V
	<u> </u>	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	22.5	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see Figure 10	1.05	1.41	1.95	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 11	-	-	2.25	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		V _{DS} = 25 V; V _{GS} = 0 V; T _j = 150 °C	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	0.95	1.25	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ °C};$ see Figure 12; see Figure 13	-	-	2.125	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12	-	0.75	0.99	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ °C};$ see Figure 12; see Figure 13	-	-	1.68	mΩ
R_{G}	internal gate resistance (AC)	f = 1 MHz	-	1.1	2.2	Ω
Dynamic char	racteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	110	-	nC
		I _D = 25 A; V _{DS} = 12 V; V _{GS} = 4.5 V; see Figure 15; see Figure 14	-	51	-	nC
		$I_D = 0$ A; $V_{DS} = 0$ V; $V_{GS} = 10$ V; see Figure 14	-	104	-	nC
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 12 V; V _{GS} = 4.5 V;	-	14.8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	10.5	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	4.4	-	nC
Q_{GD}	gate-drain charge		-	14	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 12 V; see <u>Figure 14</u> ; see Figure 15	-	2.4	-	V
C _{iss}	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	6775	-	pF
	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	1437	-	pF
Coss						•

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Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS}=12~V;~R_L=0.5~\Omega;~V_{GS}=4.5~V;$	-	42.5	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	74	-	ns
$t_{d(off)}$	turn-off delay time		-	103.5	-	ns
t _f	fall time		-	55	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	31.57	-	nC
Source-drai	in diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17	-	8.0	1.1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	48	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}$	-	60	-	nC
t _a	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S \text{ 25 A;}$ $dI_S/dt = -100 \text{ A/}\mu\text{s; } V_{DS} = 12 \text{ V;}$ see Figure 18	-	26.3	-	ns
t _b	reverse recovery fall time	$V_{GS} = 0 \text{ V; } I_S = 25 \text{ A;}$ $dI_S/dt = -100 \text{ A/}\mu\text{s; } V_{DS} = 12 \text{ V;}$ see Figure 18	-	21.7	-	ns

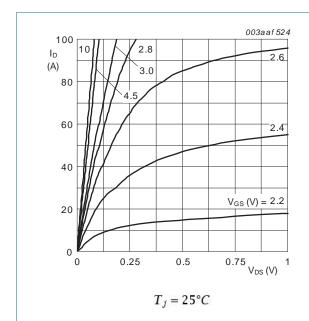
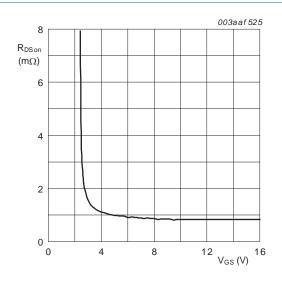


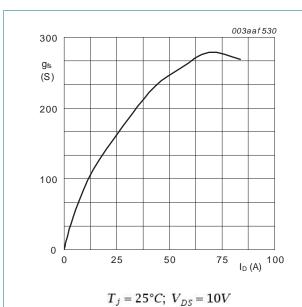
Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; \ I_D = 25A$

Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

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Forward transconductance as a function of Fig 8. drain current; typical values

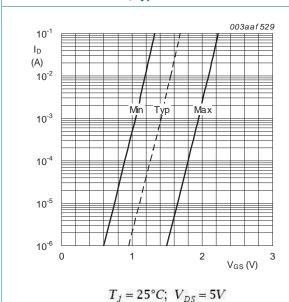
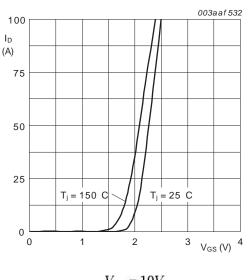


Fig 10. Sub-threshold drain current as a function of gate-source voltage



 $V_{DS} = 10V$

Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

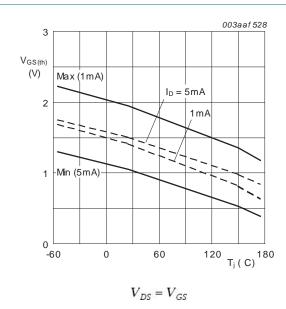


Fig 11. Gate-source threshold voltage as a function of junction temperature

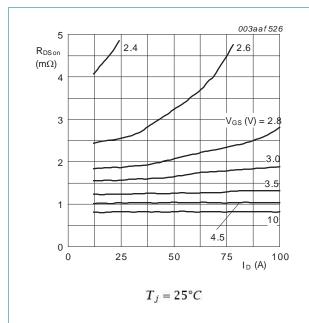


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

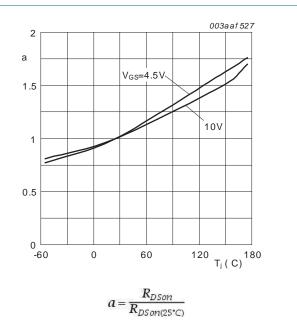


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

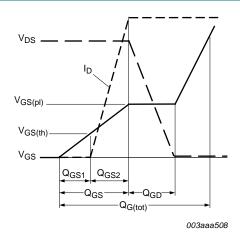
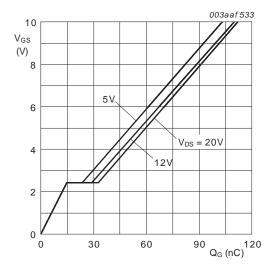


Fig 14. Gate charge waveform definitions



 $T_j = 25^{\circ}C; \ I_D = 25A$

Fig 15. Gate-source voltage as a function of gate charge; typical values

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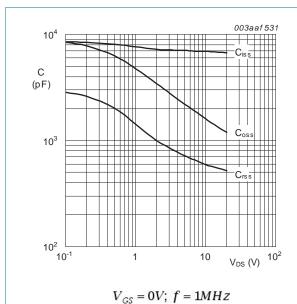


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

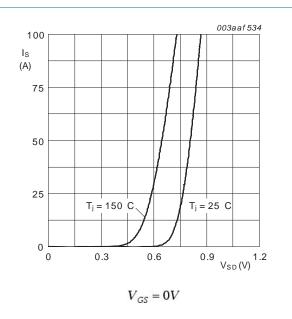


Fig 17. Source current as a function of source-drain voltage; typical values

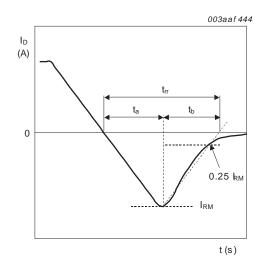
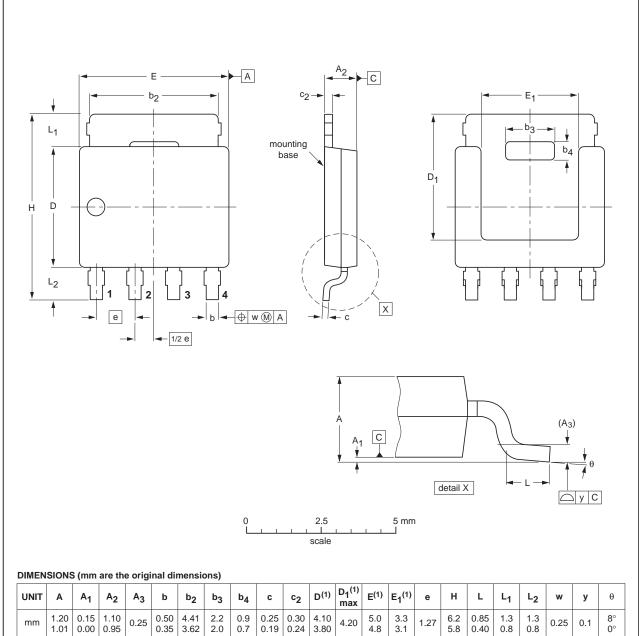


Fig 18. Reverse recovery timing definition

7. Package outline

Plastic single-ended surface-mounted package (LFPAK; Power-SO8); 4 leads

SOT669



Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT669		MO-235			06-03-16 11-03-25

Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

PSMN0R9-25YLC

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN0R9-25YLC v.2	20110704	Product data sheet	-	PSMN0R9-25YLC v.1
Modifications:	 Various changes to 	content.		
PSMN0R9-25YLC v.1	20101202	Product data sheet	-	-

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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